1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- Average forward current: I_{F(AV)} ≤ 1 A
- Reverse voltage: V_R ≤ 60 V
- Extremely low leakage current
- Low forward voltage
- High power capability due to clip-bonding technology
- Small and flat lead SMD plastic package
- AEC-Q101 qualified
- High temperature T_i ≤ 175 °C

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- Reverse polarity protection
- Low power consumption applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 170 °C; square wave	-	-	1	А
V _F	forward voltage	I _F = 1 A; T _j = 25 °C	-	605	660	mV
I _R	reverse current	V_R = 60 V; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	90	300	nA





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]	1 2	1 🔀 2
2	А	anode	SOD123W	sym001

^[1] The marking bar indicates the cathode.

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMEG6010ELR	SOD123W	plastic surface mounted package; 2 leads	SOD123W			

7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG6010ELR	K1

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
I _F	forward current	T _{sp} = 165 °C; δ = 1		-	1.41	Α
I _{F(AV)}	average forward current	δ = 0.5; f = 20 kHz; $T_{sp} \le$ 170 °C; square wave		-	1	A
		δ = 0.5; f = 20 kHz; $T_{amb} \le$ 140 °C; square wave	[1]	-	1	A
I _{FSM}	non-repetitive peak forward current	t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	50	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	680	mW
			[3]	-	1150	mW
			[1]	-	2140	mW
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1][2]	-	-	220	K/W
			[1][3]	-	-	130	K/W
			[1][4]	-	-	70	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		[5]	-	-	18	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [5] Soldering point of cathode tab.

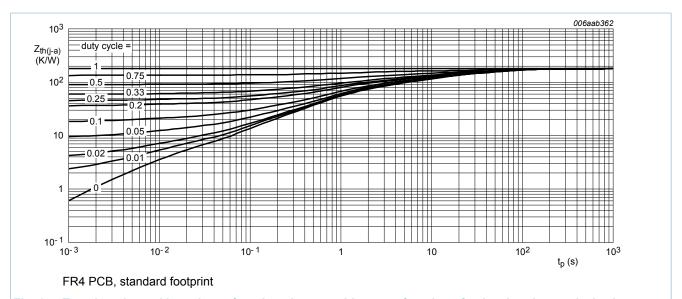


Fig. 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

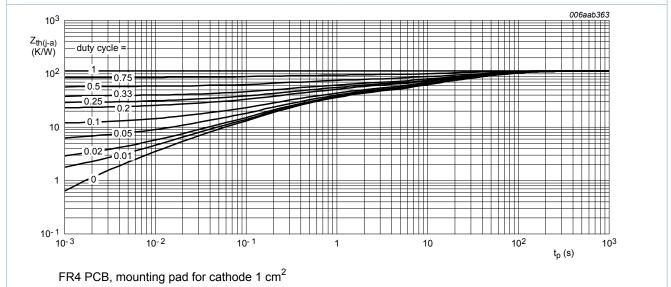
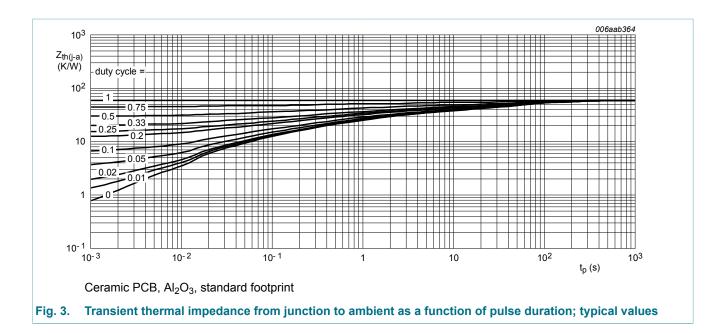


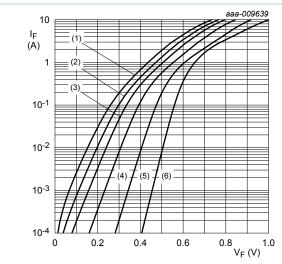
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



10. Characteristics

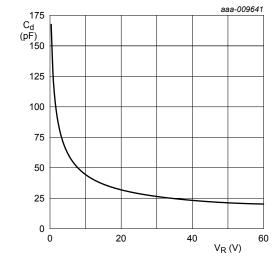
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{F}	forward voltage	I _F = 0.1 A; T _j = 25 °C	-	475	540	mV
		I _F = 0.5 A; T _j = 25 °C	-	550	605	mV
		I _F = 0.7 A; T _j = 25 °C	-	575	625	mV
		I _F = 1 A; T _j = 25 °C	-	605	660	mV
I _R	reverse current	$V_R = 5 \text{ V}; t_p \le 300 \mu\text{s}; \delta \le 0.02;$ $T_j = 25 ^{\circ}\text{C}; \text{ pulsed}$	-	5	-	nA
		$V_R = 10 \text{ V; } t_p \le 300 \mu\text{s; } \delta \le 0.02;$ $T_j = 25 \text{ °C; pulsed}$	-	6	-	nA
		$V_R = 40 \text{ V; } t_p \le 300 \mu\text{s; } \delta \le 0.02;$ $T_j = 25 \text{ °C; pulsed}$	-	25	50	nA
		V_R = 60 V; t_p ≤ 300 μs; δ ≤ 0.02; T_j = 25 °C; pulsed	-	90	300	nA
		V_R = 10 V; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_j = 125 °C; pulsed	-	25	-	μA
		$V_R = 60 \text{ V; } t_p \le 300 \mu\text{s; } \delta \le 0.02;$ $T_j = 125 \text{ °C; pulsed}$	-	120	-	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz; T _j = 25 °C	-	110	-	pF
		V _R = 4 V; f = 1 MHz; T _j = 25 °C	-	65	-	pF
		$V_R = 10 \text{ V; } f = 1 \text{ MHz; } T_j = 25 \text{ °C}$	-	45	-	pF
t _{rr}	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4.5	-	ns
V _{(BR)R}	reverse breakdown voltage	I _R = 1 mA; T _j = 25 °C	60	-	-	V
V_{FRM}	peak forward recovery voltage	$I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	580	-	mV



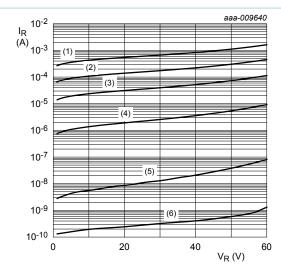
- (1) $T_i = 175 \,^{\circ}C$
- (2) $T_i = 150 \, ^{\circ}C$
- (3) $T_i = 125 \, ^{\circ}C$
- (4) $T_i = 85 \, ^{\circ}C$
- (5) $T_i = 25 \, ^{\circ}C$
- (6) $T_i = -40 \, ^{\circ}C$

Fig. 4. Forward current as a function of forward voltage; typical values



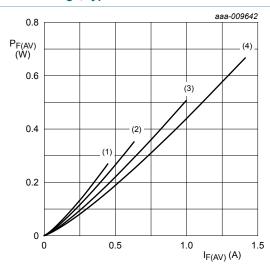
f = 1 MHz; T_{amb} = 25 °C

Fig. 6. Diode capacitance as a function of reverse voltage; typical values



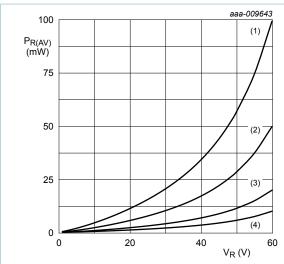
- (1) $T_i = 175 \, ^{\circ}C$
- (2) $T_i = 150 \, ^{\circ}\text{C}$
- (3) $T_i = 125 \,^{\circ}C$
- (4) $T_j = 85 \, ^{\circ}C$
- (5) $T_i = 25 \, ^{\circ}C$
- (6) $T_i = -40 \,^{\circ}\text{C}$

Fig. 5. Reverse current as a function of reverse voltage; typical values



- T_i = 175 °C
- $(1) \delta = 0.1$
- $(2) \delta = 0.2$
- $(3) \delta = 0.5$
- $(4) \delta = 1$

ig. 7. Average forward power dissipation as a function of average forward current; typical values



T_i = 150 °C

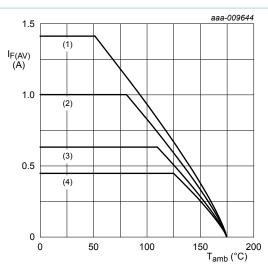
 $(1) \delta = 1$

 $(2) \delta = 0.5$

 $(3) \delta = 0.2$

 $(4) \delta = 0.1$

Fig. 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

T_i = 175 °C

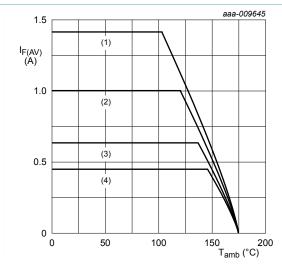
(1) $\delta = 1$ (DC)

(2) δ = 0.5; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

Fig. 9. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm²

 $T_j = 175$ °C

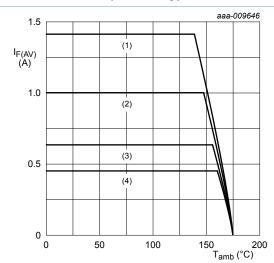
(1) $\delta = 1$ (DC)

(2) δ = 0.5; f = 20 kHz

(3) $\delta = 0.2$; f = 20 kHz

(4) δ = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al₂O₃, standard footprint

T_i = 175 °C

(1) $\delta = 1$ (DC)

(2) δ = 0.5; f = 20 kHz

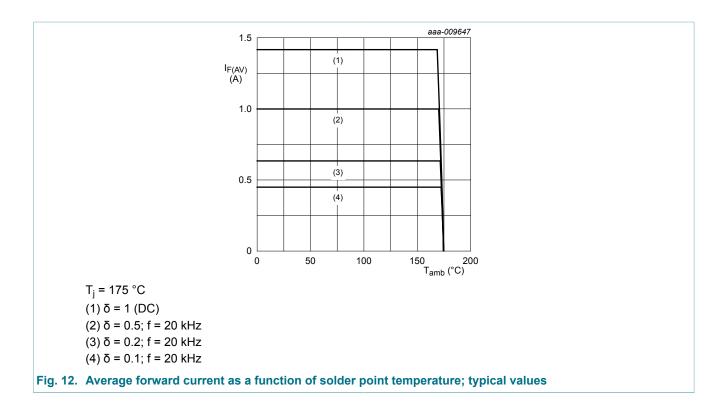
(3) δ = 0.2; f = 20 kHz

(4) $\delta = 0.1$; f = 20 kHz

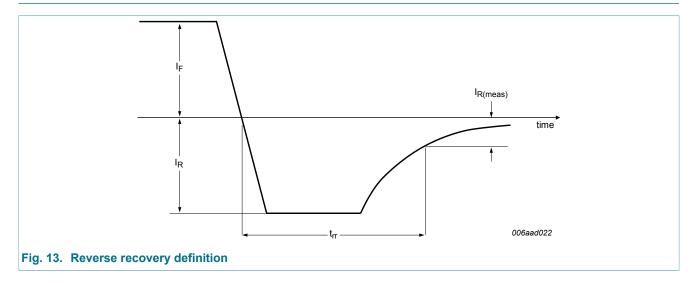
Fig. 11. Average forward current as a function of ambient temperature; typical values

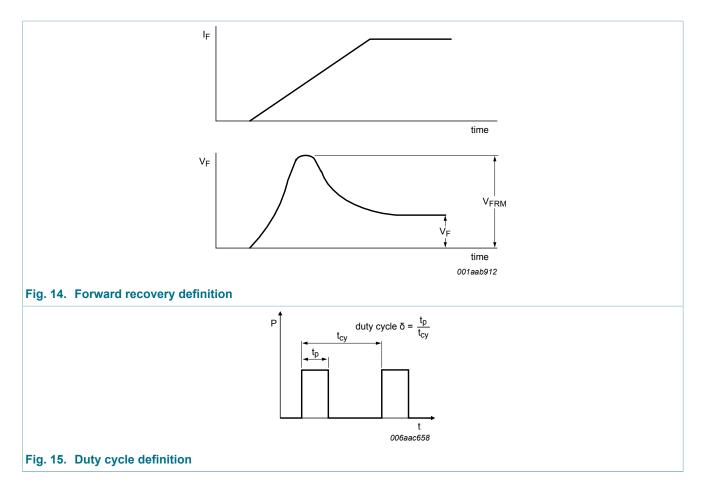
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60 V, 1 A low leakage current Schottky barrier rectifier



11. Test information





The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline

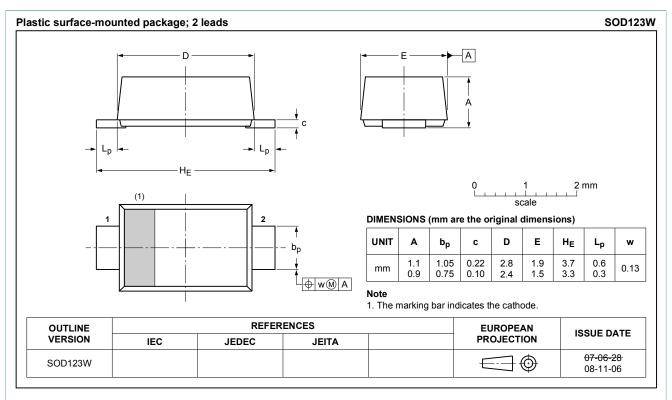
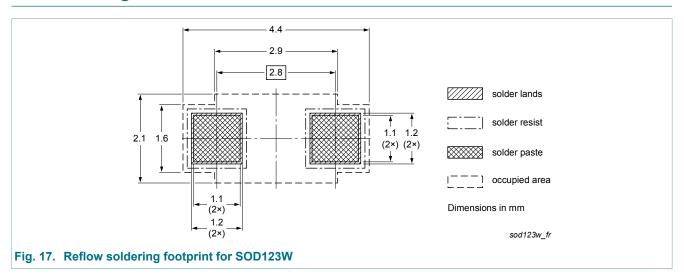


Fig. 16. Package outline SOD123W

13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6010ELR v.2	20140603	Product data sheet	-	PMEG6010ELR v.1
Modifications:	Product specification updated			
PMEG6010ELR v.1	20131108	Preliminary data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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NXP Semiconductors PMEG6010ELR

60 V, 1 A low leakage current Schottky barrier rectifier

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